



CPH3356

P-Channel Power MOSFET -20V, -2.5A, 137mΩ, Single CPH3

ON Semiconductor®

<http://onsemi.com>

Features

- 1.8V drive
- Halogen free compliance
- Protection diode in

Specifications

Absolute Maximum Ratings at Ta=25°C

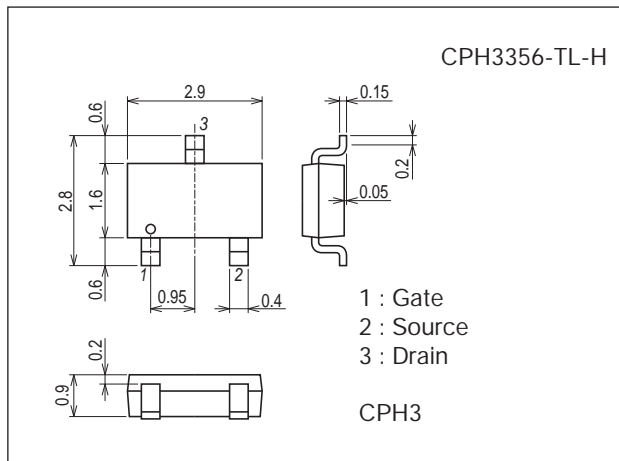
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-20	V
Gate-to-Source Voltage	V _{GSS}		±10	V
Drain Current (DC)	I _D		-2.5	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	-10	A
Allowable Power Dissipation	P _D	When mounted on ceramic substrate (900mm ² ×0.8mm)	1.0	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ)

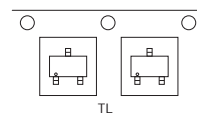
7015A-004



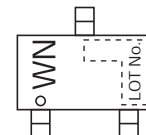
Product & Package Information

- Package : CPH3
- JEITA, JEDEC : SC-59, TO-236, SOT-23
- Minimum Packing Quantity : 3,000 pcs./reel

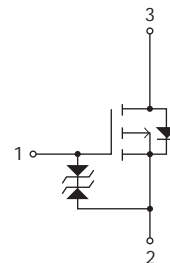
Packing Type: TL



Marking



Electrical Connection

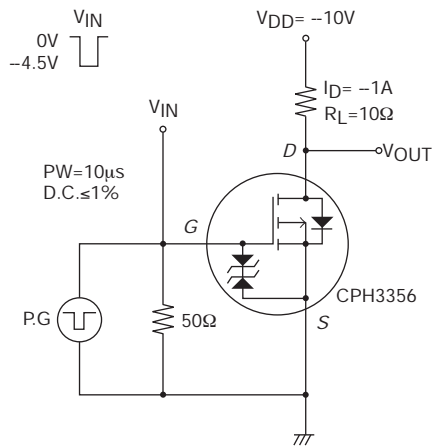


CPH3356

Electrical Characteristics at Ta=25°C

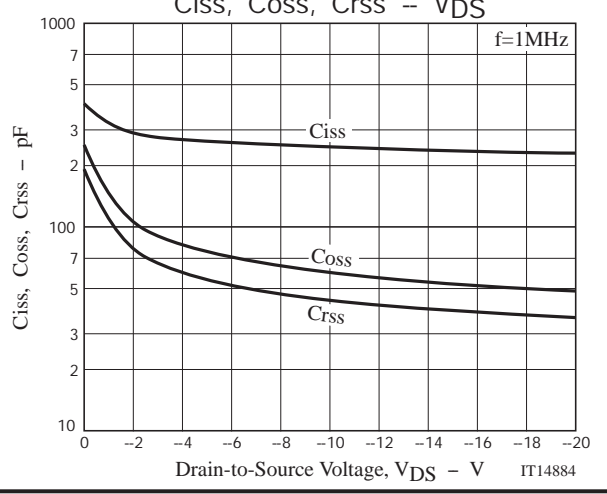
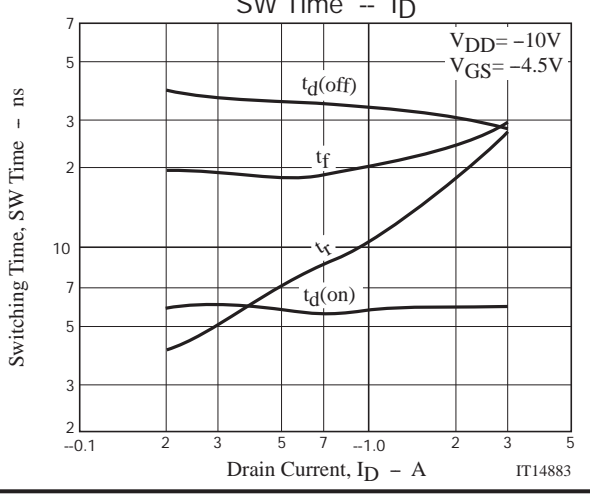
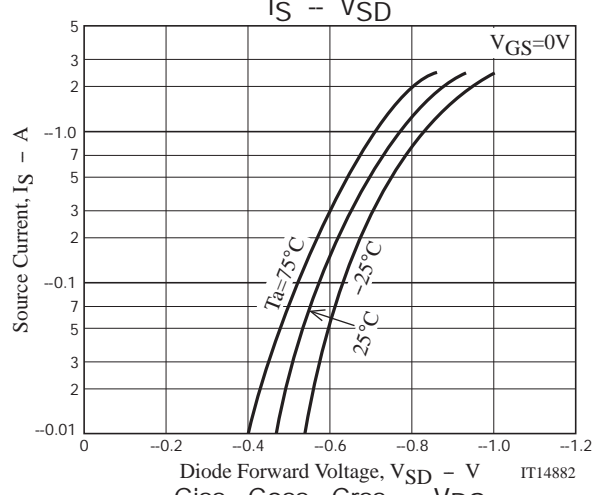
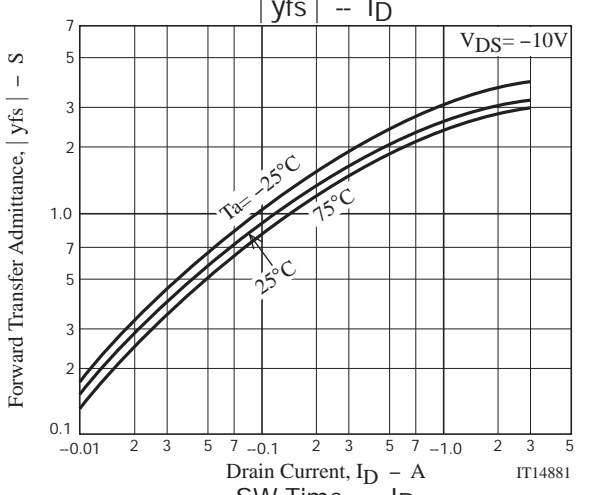
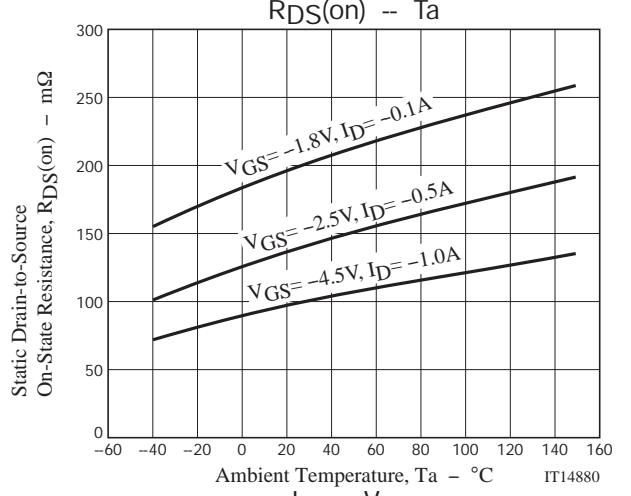
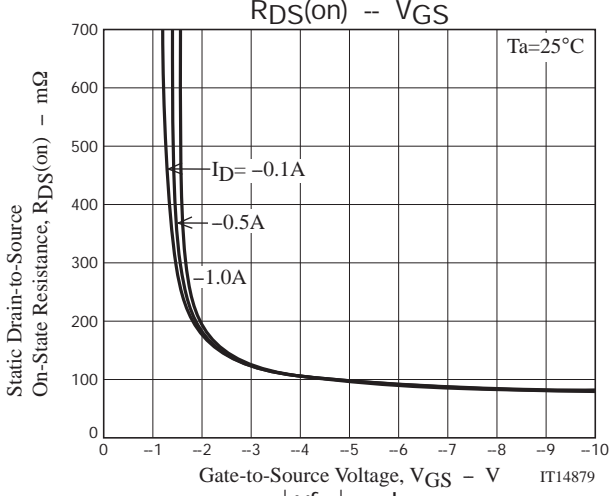
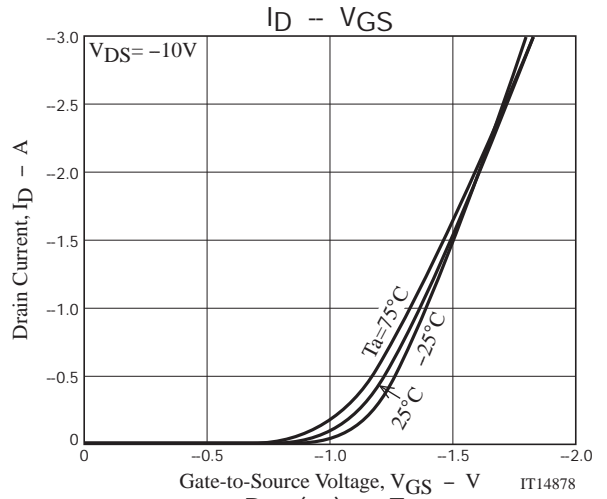
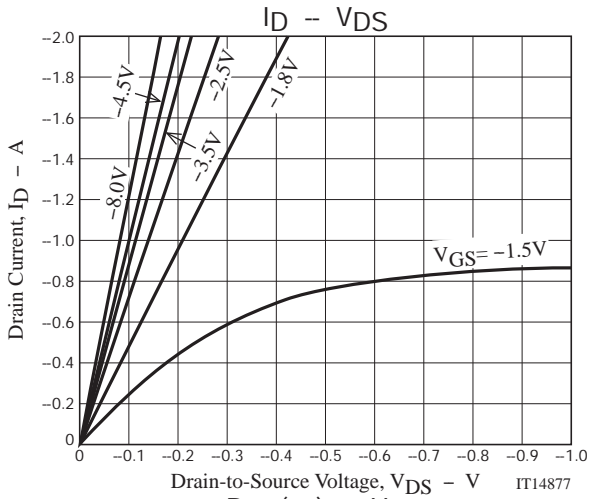
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =-1mA, V _{GS} =0V	-20			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V, V _{GS} =0V			-1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±8V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =-10V, I _D =-1mA	-0.4		-1.4	V
Forward Transfer Admittance	y _{fs}	V _{DS} =-10V, I _D =-1A		2.7		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =-1A, V _{GS} =-4.5V		105	137	mΩ
	R _{DS(on)2}	I _D =-0.5A, V _{GS} =-2.5V		145	203	mΩ
	R _{DS(on)3}	I _D =-0.1A, V _{GS} =-1.8V		215	323	mΩ
Input Capacitance	C _{iss}	V _{DS} =-10V, f=1MHz		250		pF
Output Capacitance	C _{oss}			60		pF
Reverse Transfer Capacitance	C _{rss}			45		pF
Turn-ON Delay Time	t _{d(on)}		See specified Test Circuit.		5.7	
Rise Time	t _r			11		ns
Turn-OFF Delay Time	t _{d(off)}			34		ns
Fall Time	t _f			20		ns
Total Gate Charge	Q _g	V _{DS} =-10V, V _{GS} =-4.5V, I _D =-2.5A			3.3	
Gate-to-Source Charge	Q _{gs}			0.65		nC
Gate-to-Drain "Miller" Charge	Q _{gd}			0.72		nC
Diode Forward Voltage	V _{SD}	I _S =-2.5A, V _{GS} =0V		-0.87	-1.5	V

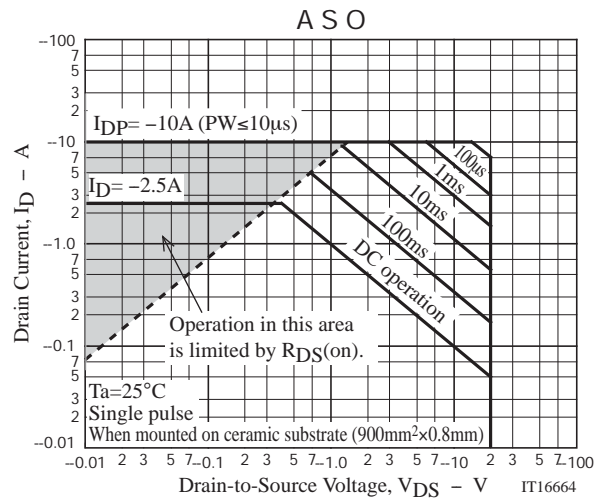
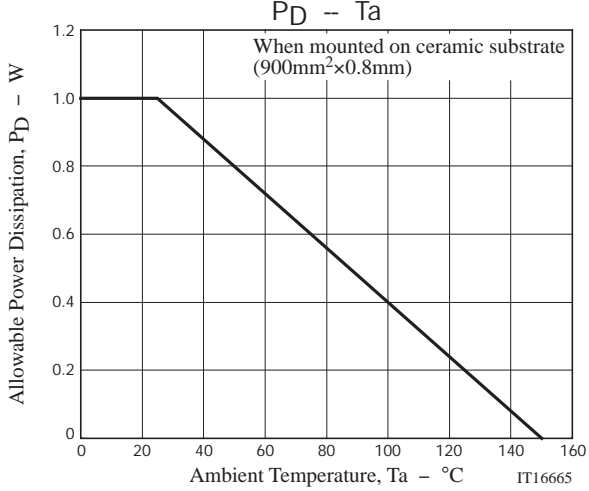
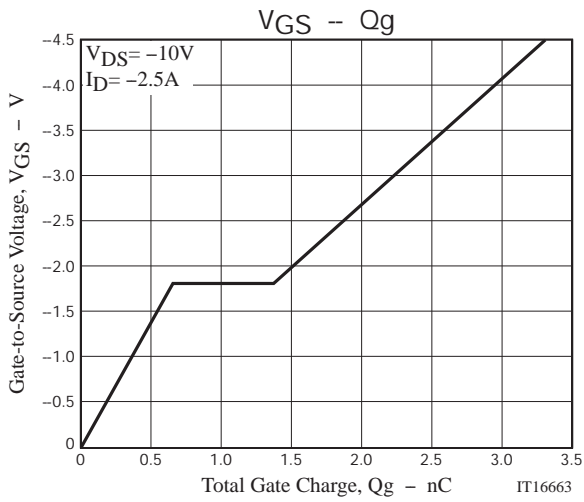
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
CPH3356-TL-H	CPH3	3,000pcs./reel	Pb Free and Halogen Free





Embossed Taping Specification
CPH3356-TL-H

1. Packing Format

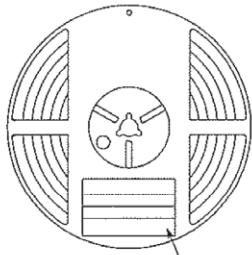
Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
CPH3	CPH3	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

Reel label, Inner box label
(unit:mm)

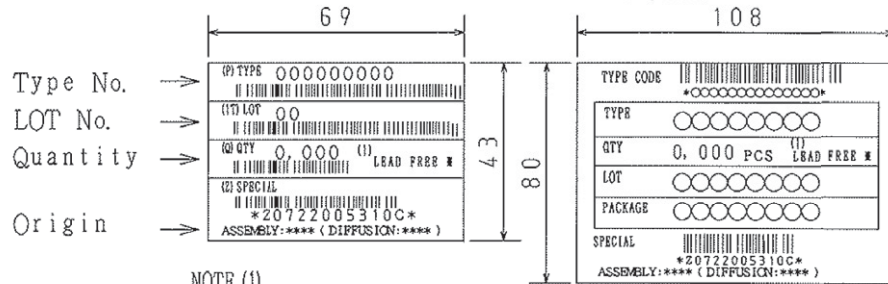
Outer box label

It is a label at the time of factory shipments.
The form of a label may change in physical distribution process.

Packing method



Reel label



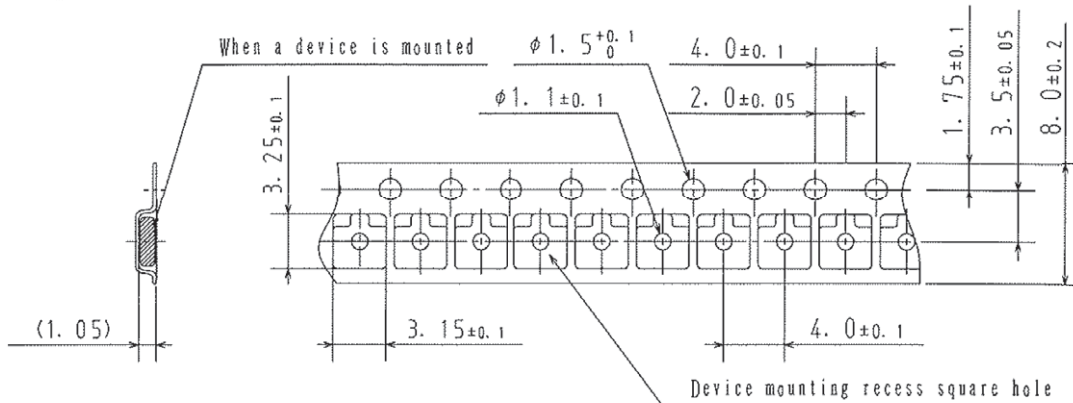
NOTE (1)

The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

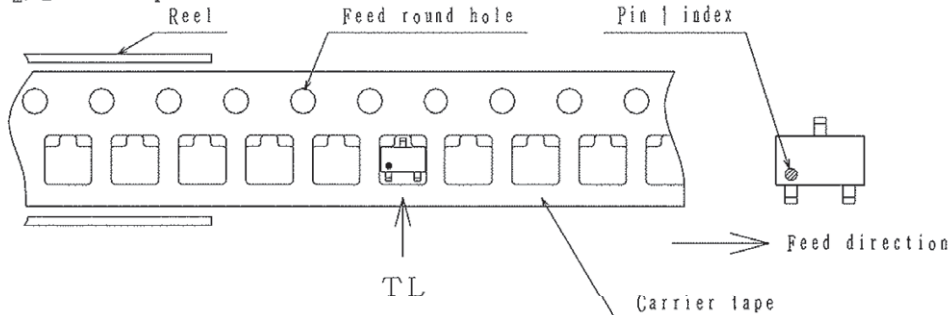
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)

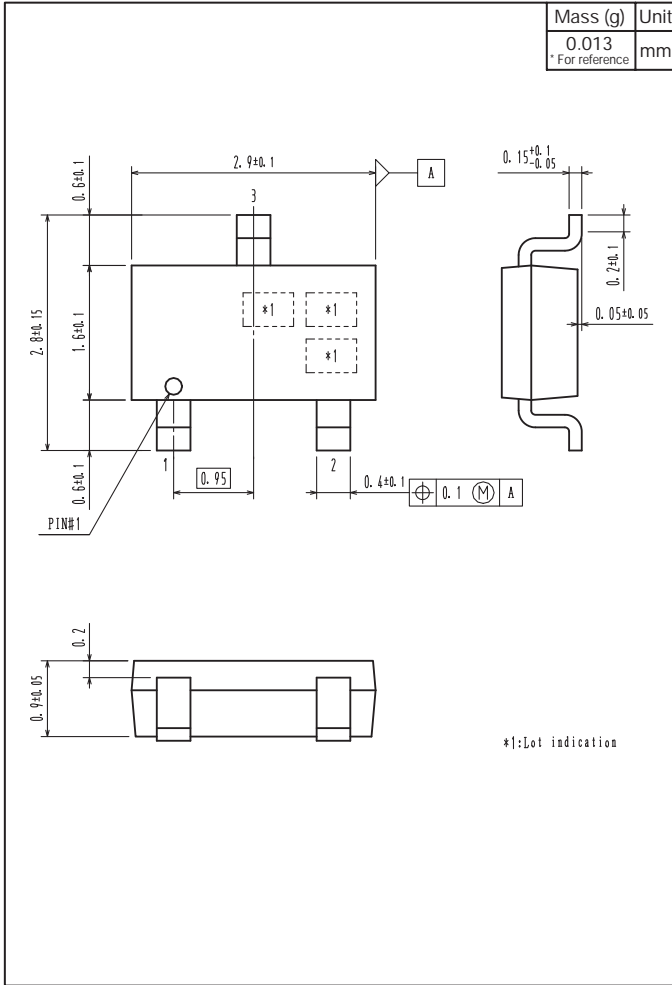


2-2. Device placement direction

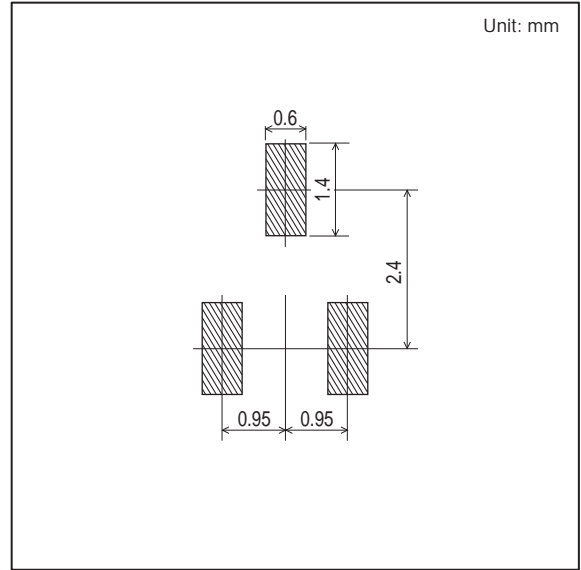


Those with one electrode terminal on the feed hole side.....TL

Outline Drawing
CPH3356-TL-H



Land Pattern Example



Note on usage : Since the CPH3356 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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